

2SD1576

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

■ Features

- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- “Full Pack” package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	1500	V
Collector-emitter voltage	V_{CES}	1500	V
	V_{CFO}	700	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Peak collector current	I_{CP}^*	6	A
Peak base current	I_{BP}	2.5	A
Reverse peak base current	I_{BP}	-1.5	A
Collector power dissipation	$T_C = 25^\circ C$	80	W
	$T_A = 25^\circ C$	2.5	
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ C$

^{*} Non repetitive peak value

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=750V, I_L=0$			50	μA
		$V_{CB}=1500V, I_E=0$			1	mA
Emitter-base voltage	V_{EBQ}	$I_E=1mA, I_C=0$	6			V
DC current gain	h_{FF}	$V_{CE}=5V, I_C=2A$	2		5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A, I_B=1A$			5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2A, I_B=1A$			1.5	V
Transition frequency	f_T	$V_{CE}=10V, I_C=0.5A, f=0.5MHz$		2		MHz
Fall time	t_f	$I_C=2.5A, I_{Bend}=1.1A$			1	μs
Storage time	t_{sig}	$L_B=10\mu H$			9	μs

■ Package Dimensions



